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Kind regards,

Team Nexperia

# PMPB15XP

12 V, single P-channel Trench MOSFET

22 November 2012

Product data sheet

## 1. Product profile

### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- 1.5 kV ESD protection (human body model)
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

### 1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

### 1.4 Quick reference data

Table 1. Quick reference data

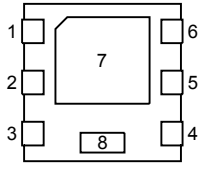
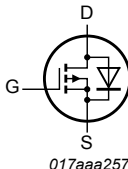
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	-12	V
$V_{GS}$	gate-source voltage		-12	-	12	V
$I_D$	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	-11.8	A
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = -4.5\text{ V}; I_D = -8.2\text{ A}; T_j = 25\text{ °C}$	-	15	19	m $\Omega$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	 <p>Transparent top view <b>DFN2020MD-6 (SOT1220)</b></p>	 <p>017aaa257</p>
2	D	drain		
3	G	gate		
4	S	source		
5	D	drain		
6	D	drain		
7	D	drain		
8	S	source		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMPB15XP	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PMPB15XP	1A

## 5. Limiting values

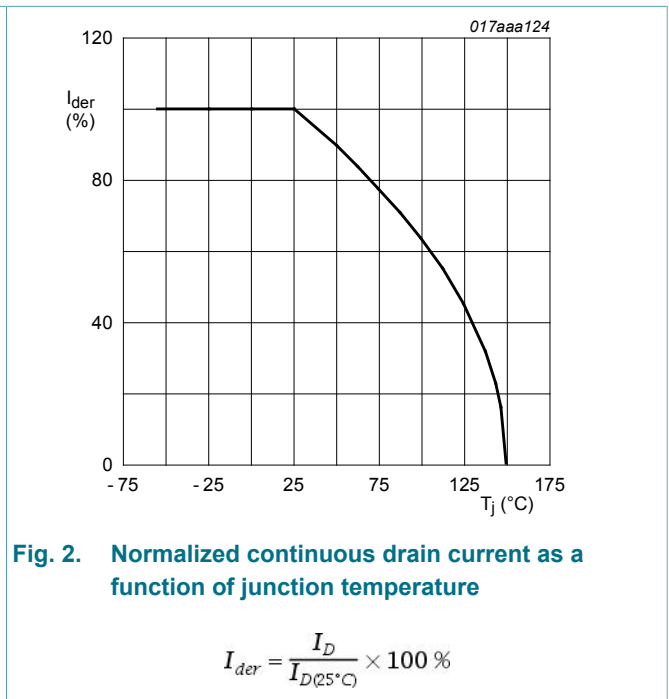
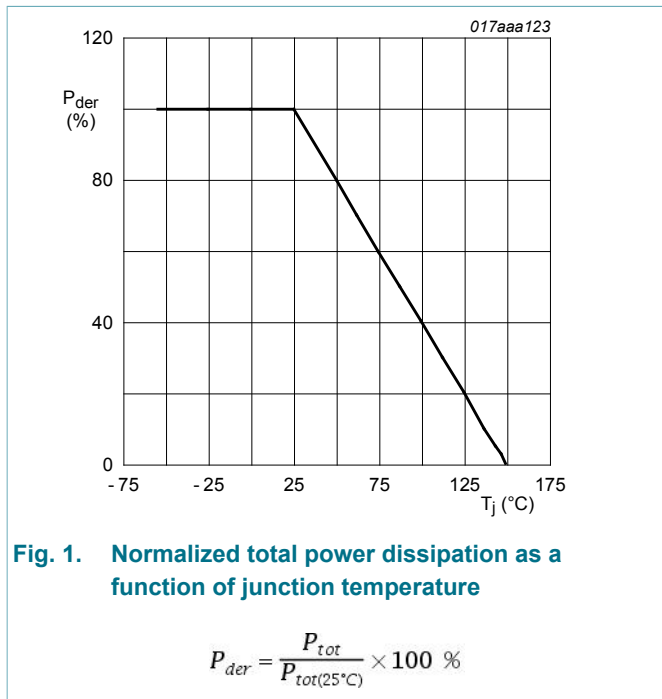
Table 5. Limiting values

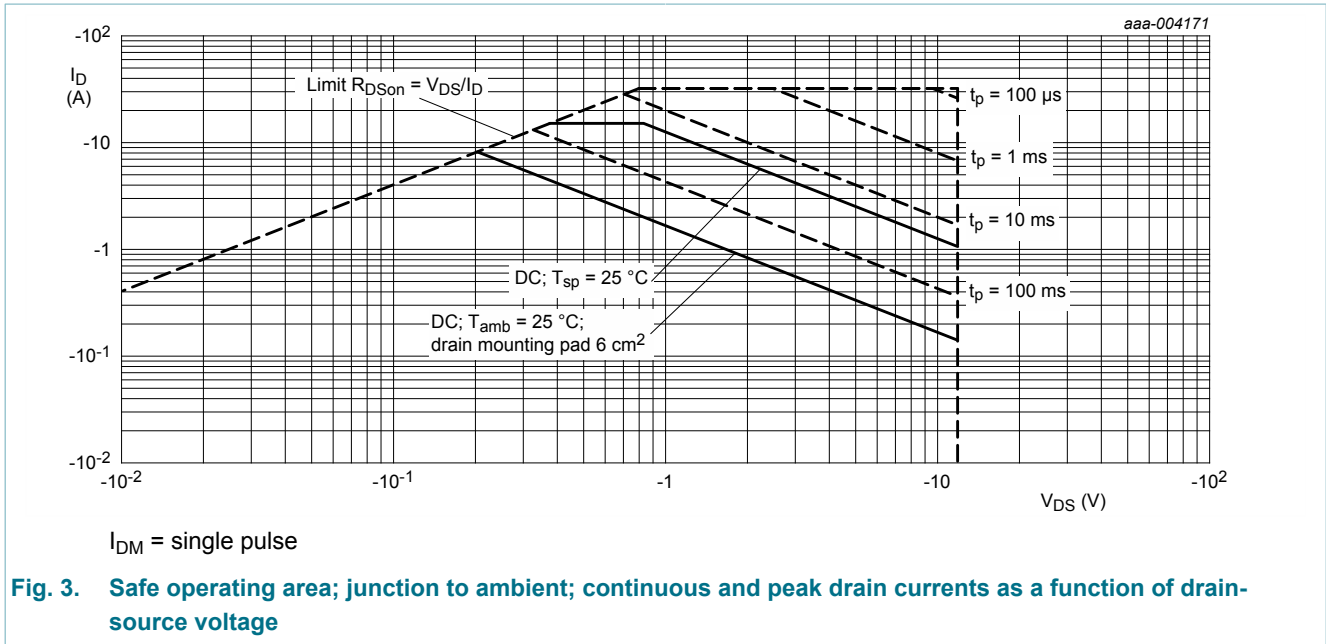
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$	-	-12	V	
$V_{GS}$	gate-source voltage		-12	12	V	
$I_D$	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}; t \leq 5\text{ s}$	[1]	-	-11.8	A
		$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	-8.2	A
		$V_{GS} = -4.5\text{ V}; T_{amb} = 100\text{ }^\circ\text{C}$	[1]	-	-5.2	A
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ }^\circ\text{C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$	-	-33	A	
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	1.7	W

Symbol	Parameter	Conditions		Min	Max	Unit
		$T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	3.5	W
		$T_{sp} = 25\text{ °C}$		-	12.5	W
$T_j$	junction temperature			-55	150	°C
$T_{amb}$	ambient temperature			-55	150	°C
$T_{stg}$	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
$I_S$	source current	$T_{amb} = 25\text{ °C}$	[1]	-	-1.9	A

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





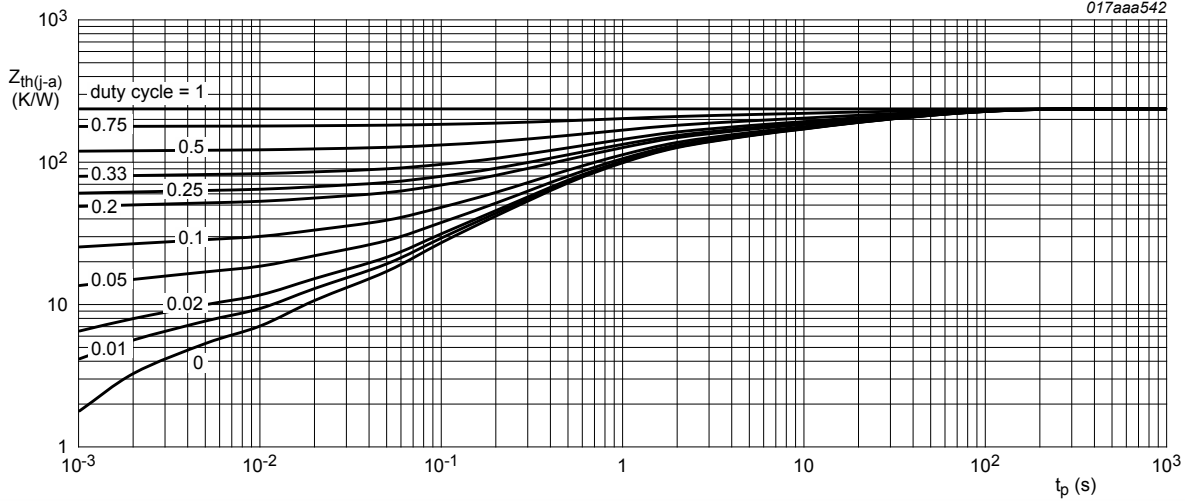
## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	235	270	K/W
			[2]	-	67	74	K/W
		in free air; $t \leq 5\text{ s}$	[2]	-	33	36	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	5	10	K/W

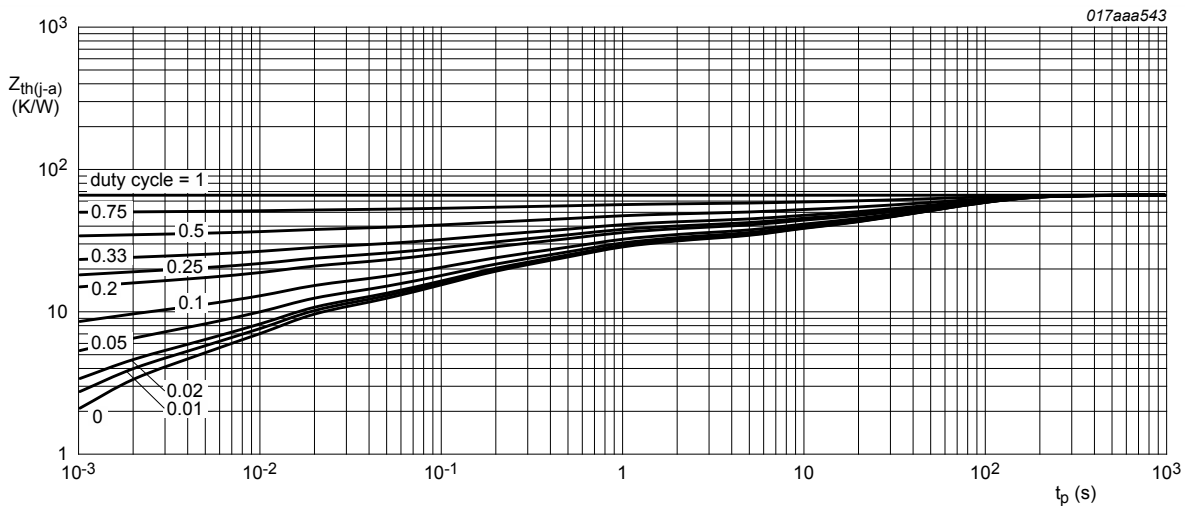
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain  $6\text{ cm}^2$ .



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 7. Characteristics

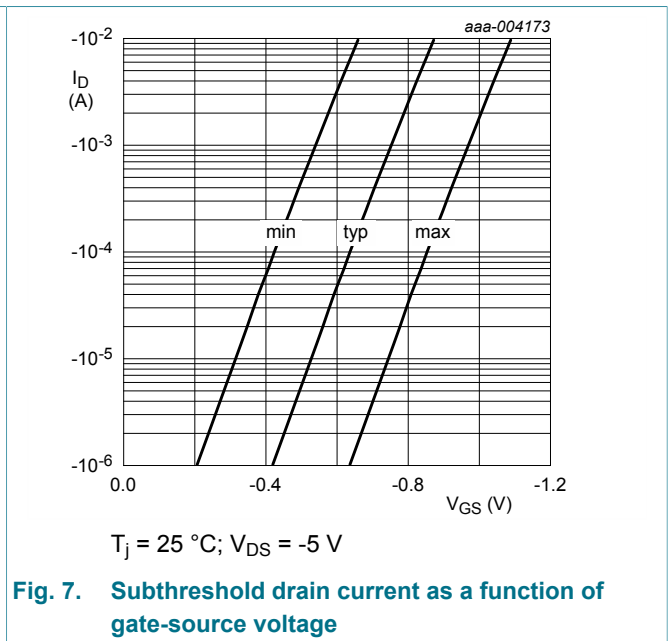
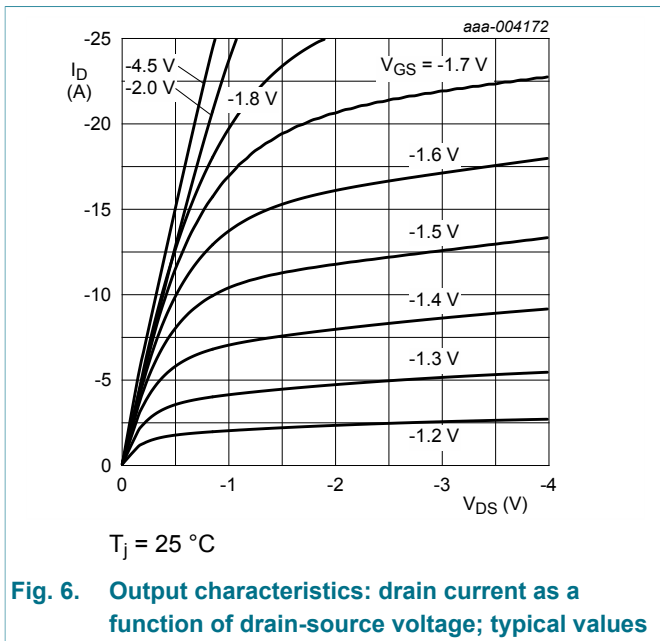
Table 7. Characteristics

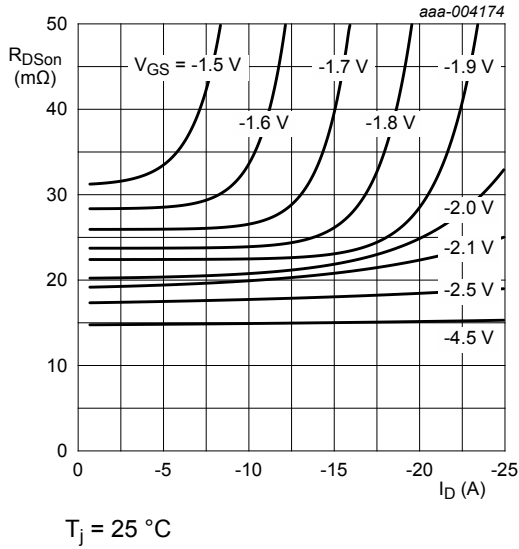
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-12	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	-0.47	-0.68	-0.9	V
$I_{DSS}$	drain leakage current	$V_{DS} = -12 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-1	$\mu A$
		$V_{DS} = -12 V; V_{GS} = 0 V; T_j = 150 \text{ }^\circ C$	-	-	-100	$\mu A$

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -8.2 A; T <sub>j</sub> = 25 °C	-	15	19	mΩ
		V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -8.2 A; T <sub>j</sub> = 150 °C	-	20	25	mΩ
		V <sub>GS</sub> = -2.5 V; I <sub>D</sub> = -3.9 A; T <sub>j</sub> = 25 °C	-	17	20	mΩ
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -3.9 A; T <sub>j</sub> = 25 °C	-	21	33	mΩ
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -8.2 A; T <sub>j</sub> = 25 °C	-	40	-	S

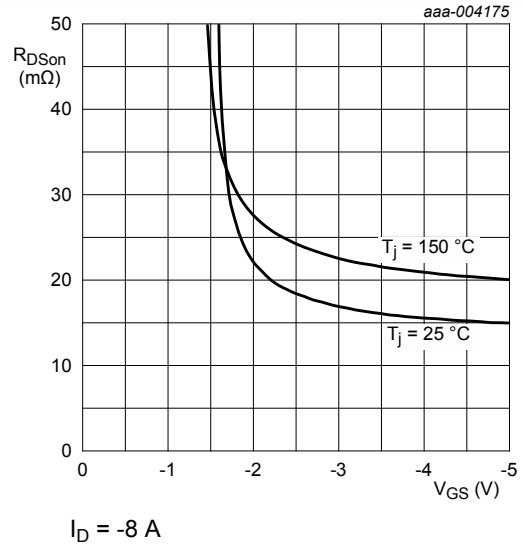
Dynamic characteristics						
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = -6 V; I <sub>D</sub> = -8.2 A; V <sub>GS</sub> = -4.5 V; T <sub>j</sub> = 25 °C	-	67	100	nC
Q <sub>GS</sub>	gate-source charge		-	5.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	7.3	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -6 V; f = 1 MHz; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2875	-	pF
C <sub>oss</sub>	output capacitance		-	570	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	530	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = -6 V; I <sub>D</sub> = -8.2 A; V <sub>GS</sub> = -4.5 V; R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	18	-	ns
t <sub>r</sub>	rise time		-	90	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	85	-	ns
t <sub>f</sub>	fall time		-	57	-	ns

Source-drain diode						
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -1.9 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-0.6	-1.2	V

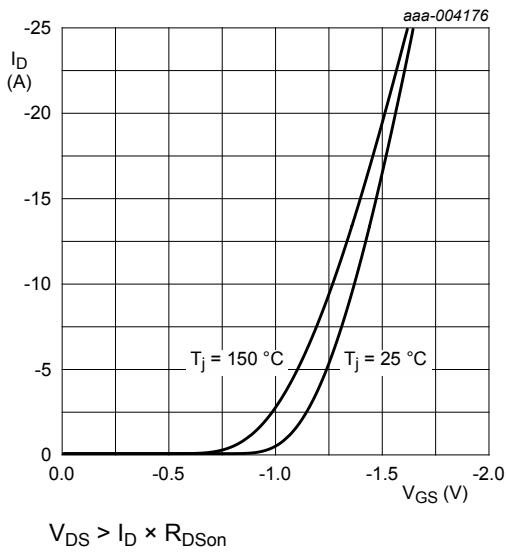




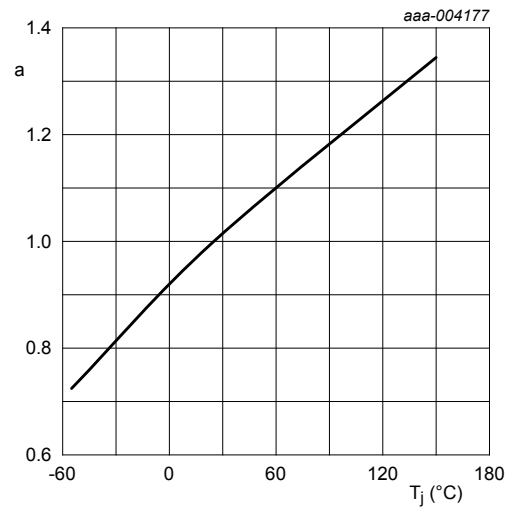
**Fig. 8. Drain-source on-state resistance as a function of drain current; typical values**



**Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**



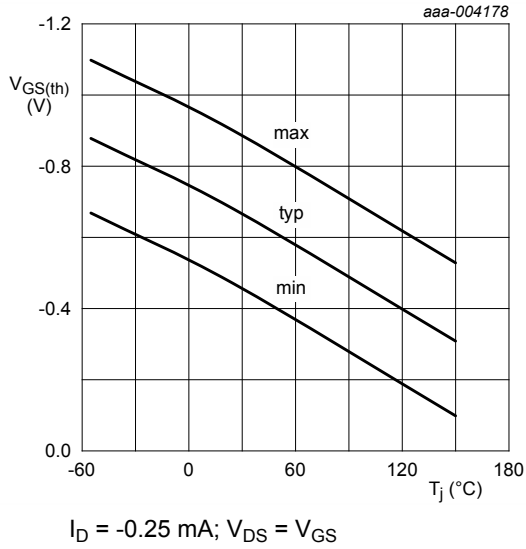
**Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



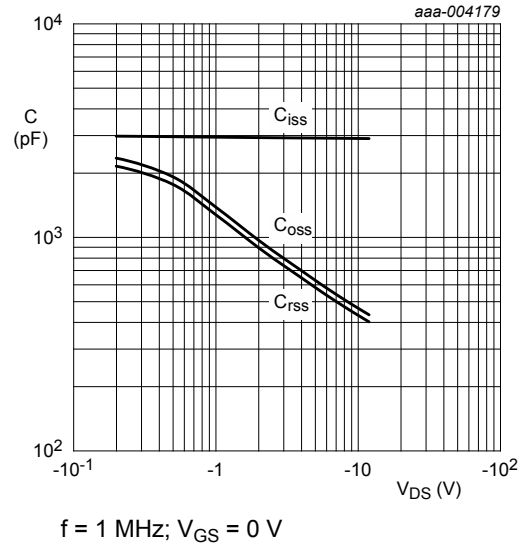
**Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

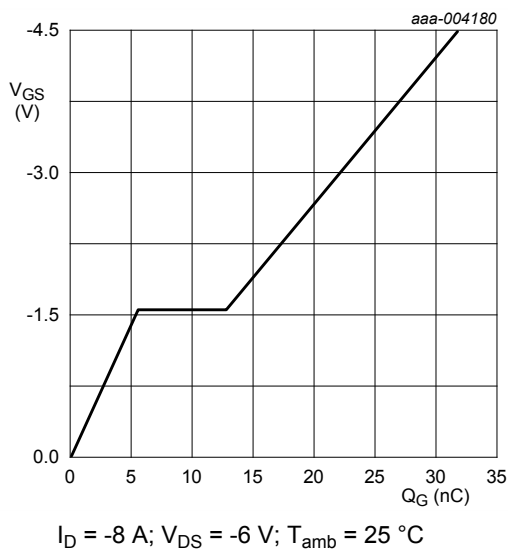




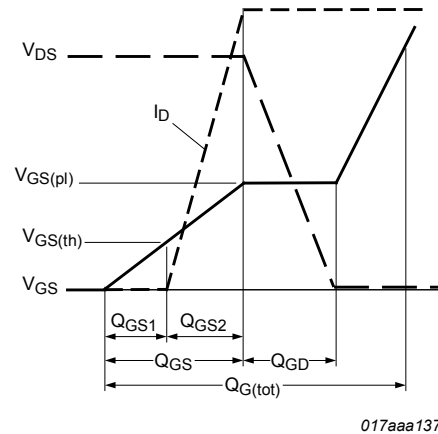
**Fig. 12. Gate-source threshold voltage as a function of junction temperature**



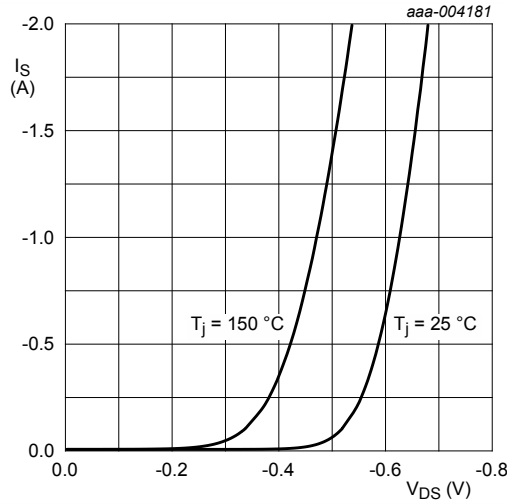
**Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



**Fig. 14. Gate-source voltage as a function of gate charge; typical values**



**Fig. 15. Gate charge waveform definitions**



$V_{GS} = 0\text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

### 8. Test information

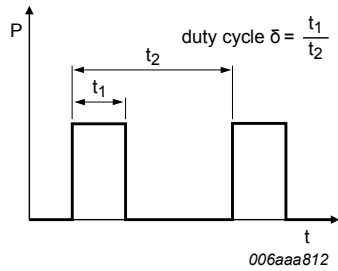


Fig. 17. Duty cycle definition

### 9. Package outline

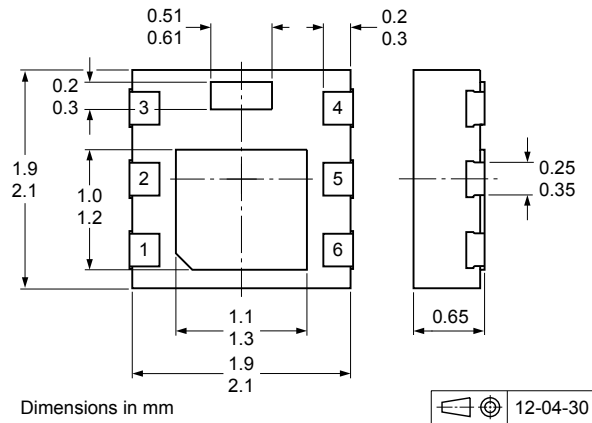


Fig. 18. Package outline DFN2020MD-6 (SOT1220)

### 10. Soldering

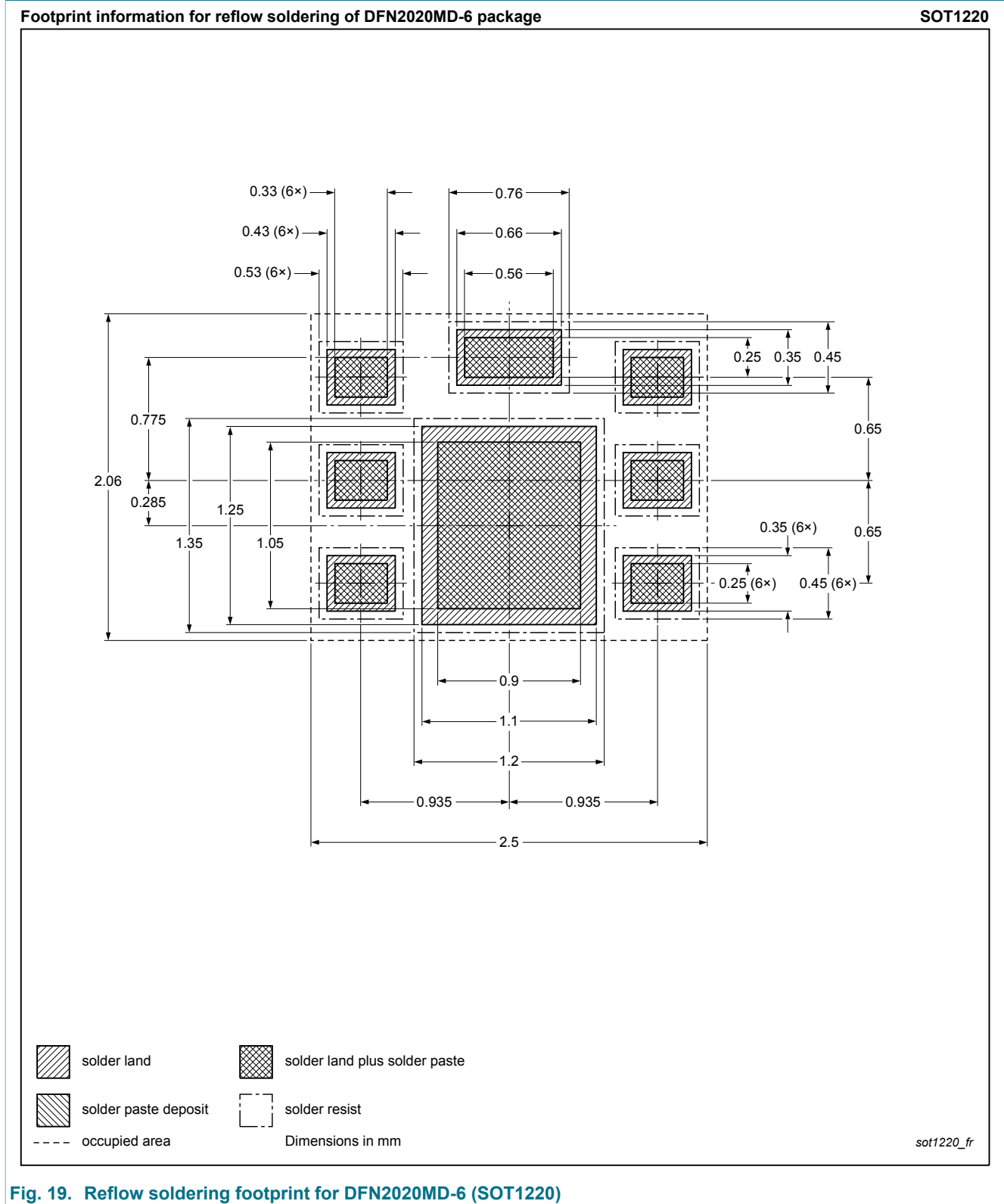


Fig. 19. Reflow soldering footprint for DFN2020MD-6 (SOT1220)

## 11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB15XP v.3	20121122	Product data sheet	-	PMPB15XP v.2
Modifications:	<ul style="list-style-type: none"><li>Table 7 "Characteristics": <math>R_{DSon}</math> at <math>V_{GS} = -1.8</math> V corrected.</li></ul>			
PMPB15XP v.2	20120719	Product data sheet	-	PMPB15XP v.1
PMPB15XP v.1	20120706	Preliminary data sheet	-	-

## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 22 November 2012

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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